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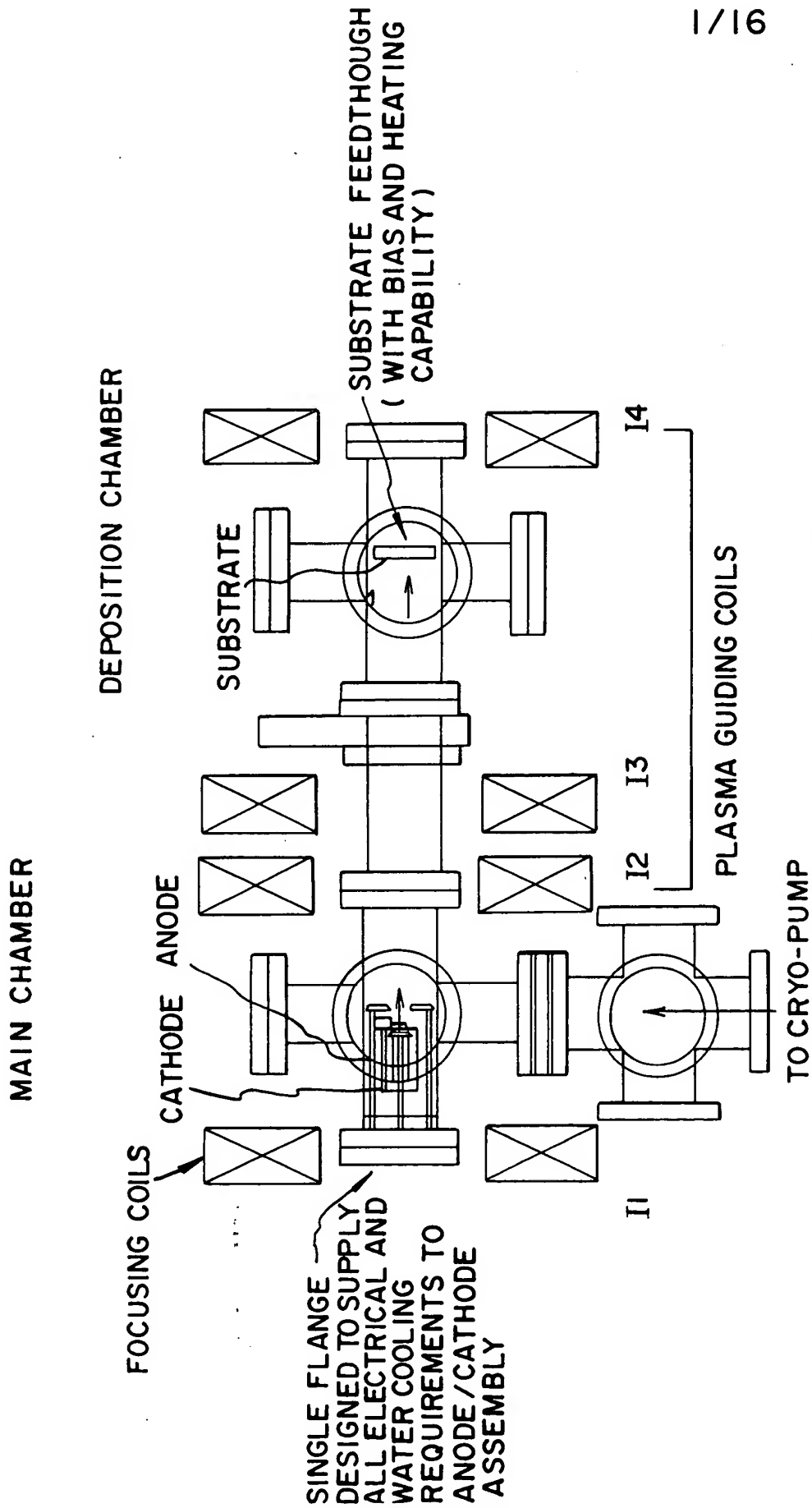


Fig.1

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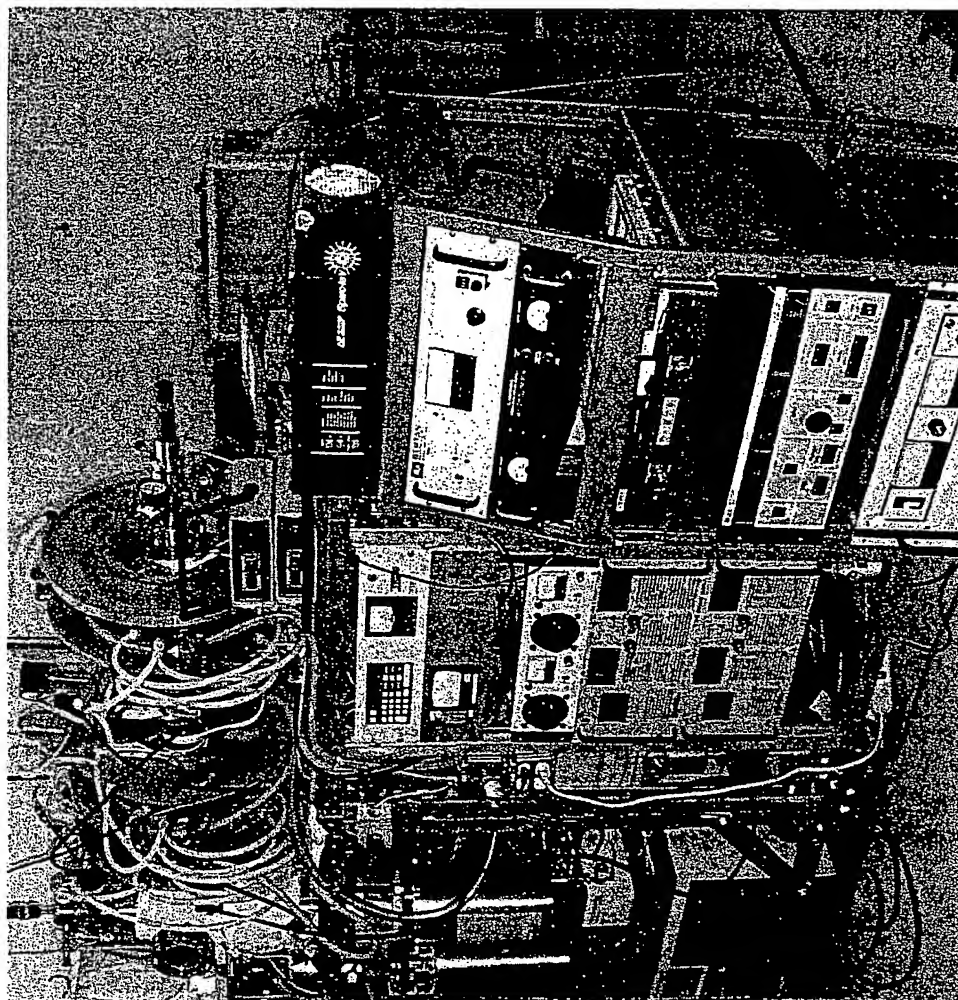


Fig. 2

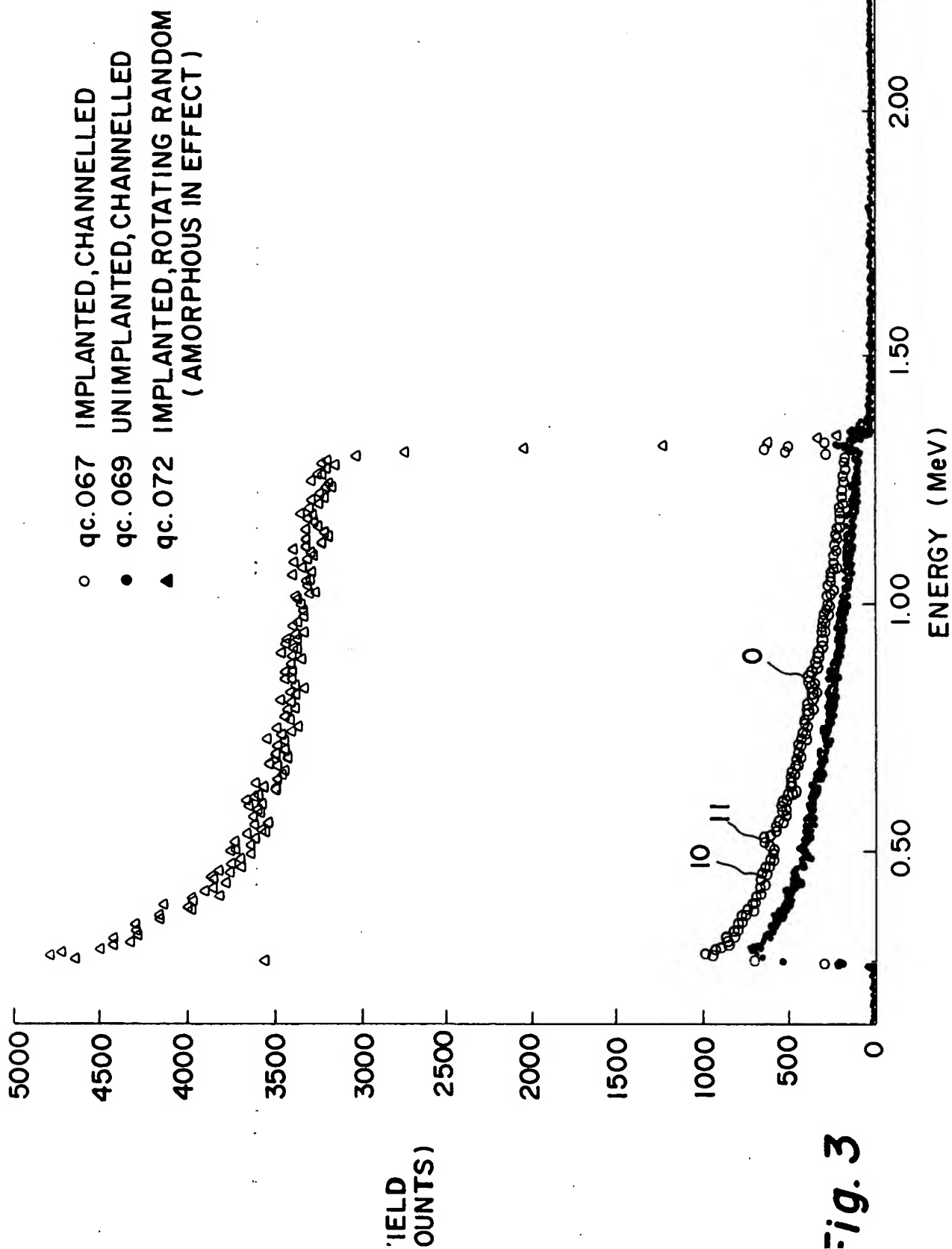
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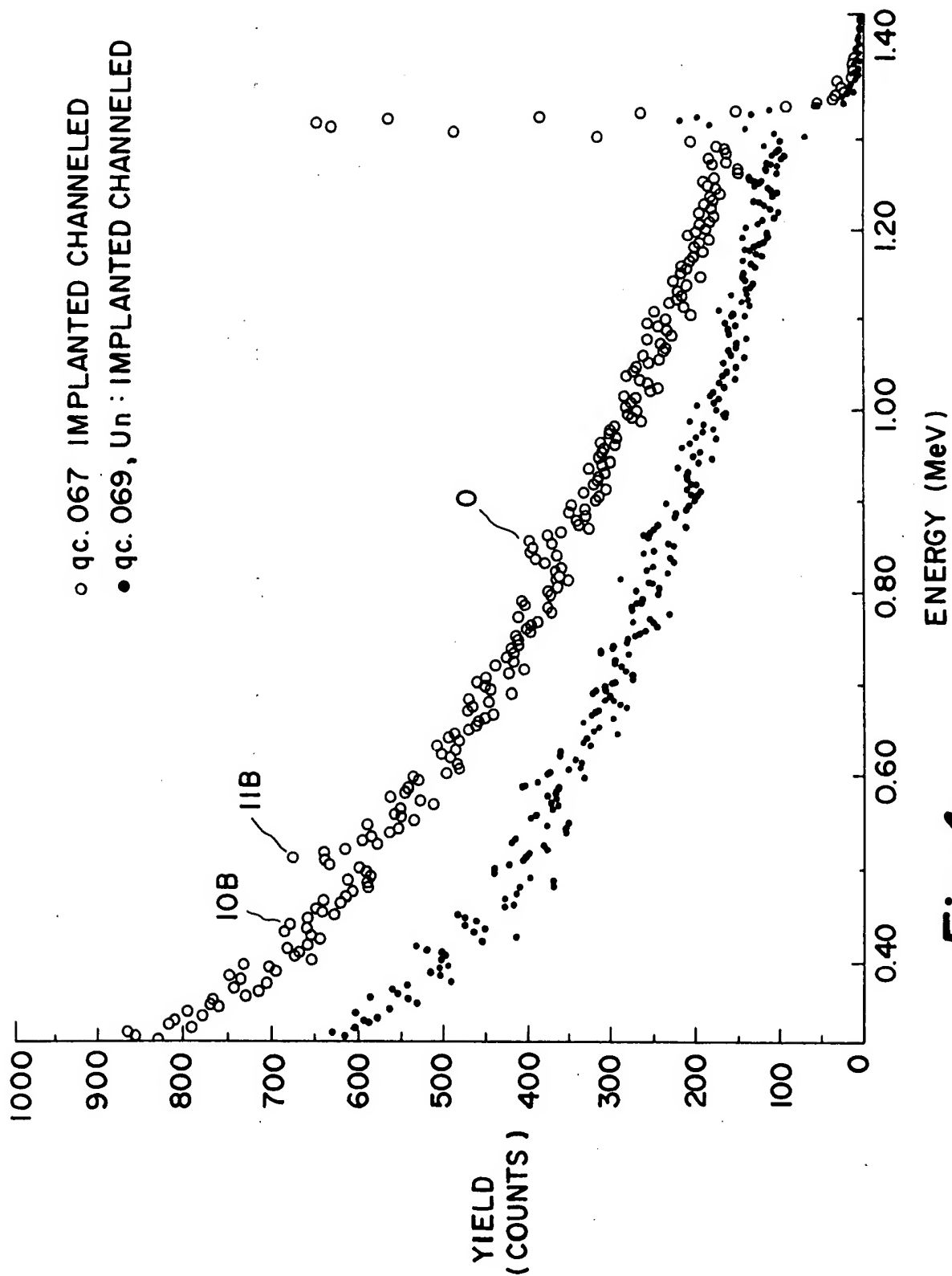


Fig. 4

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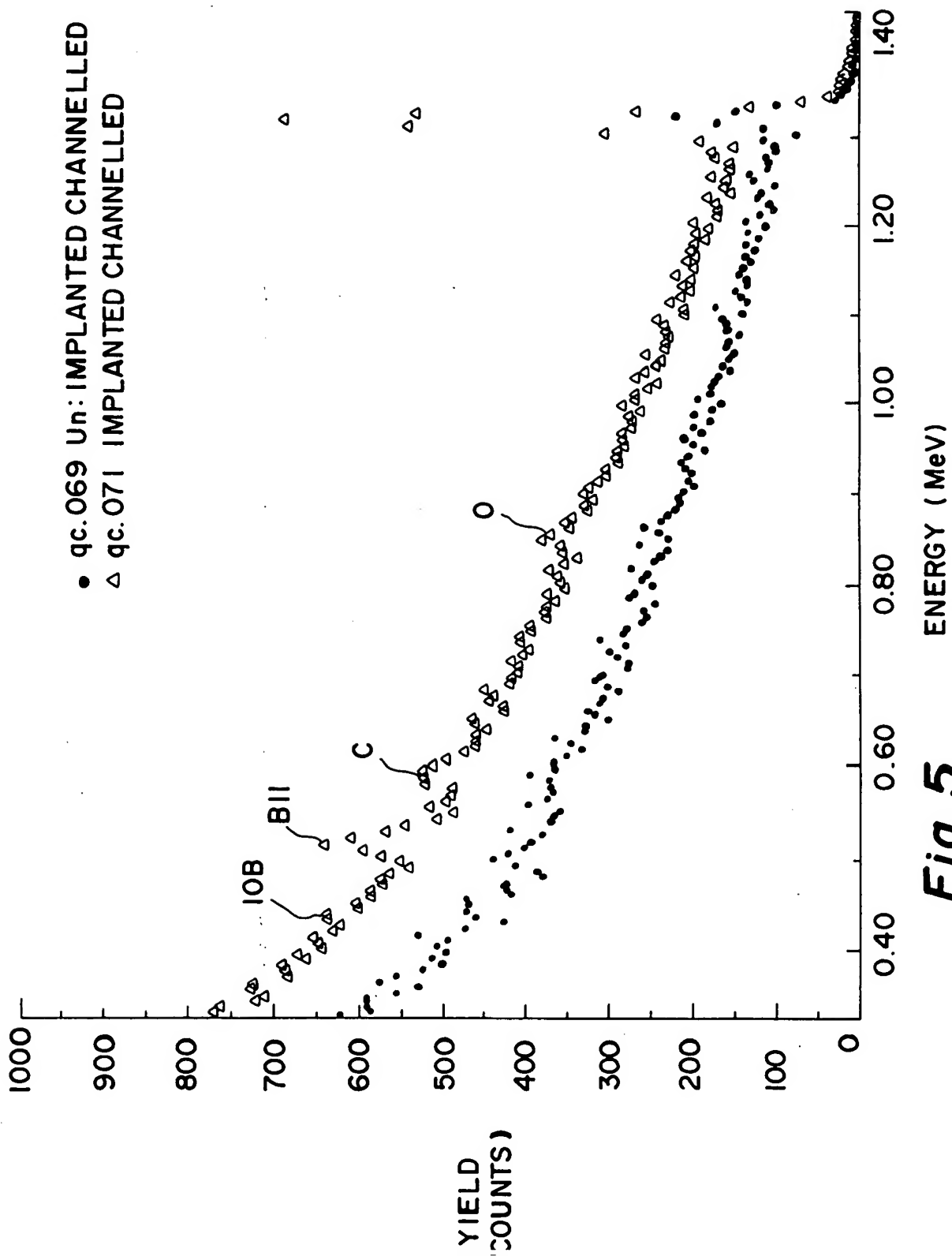


Fig. 5



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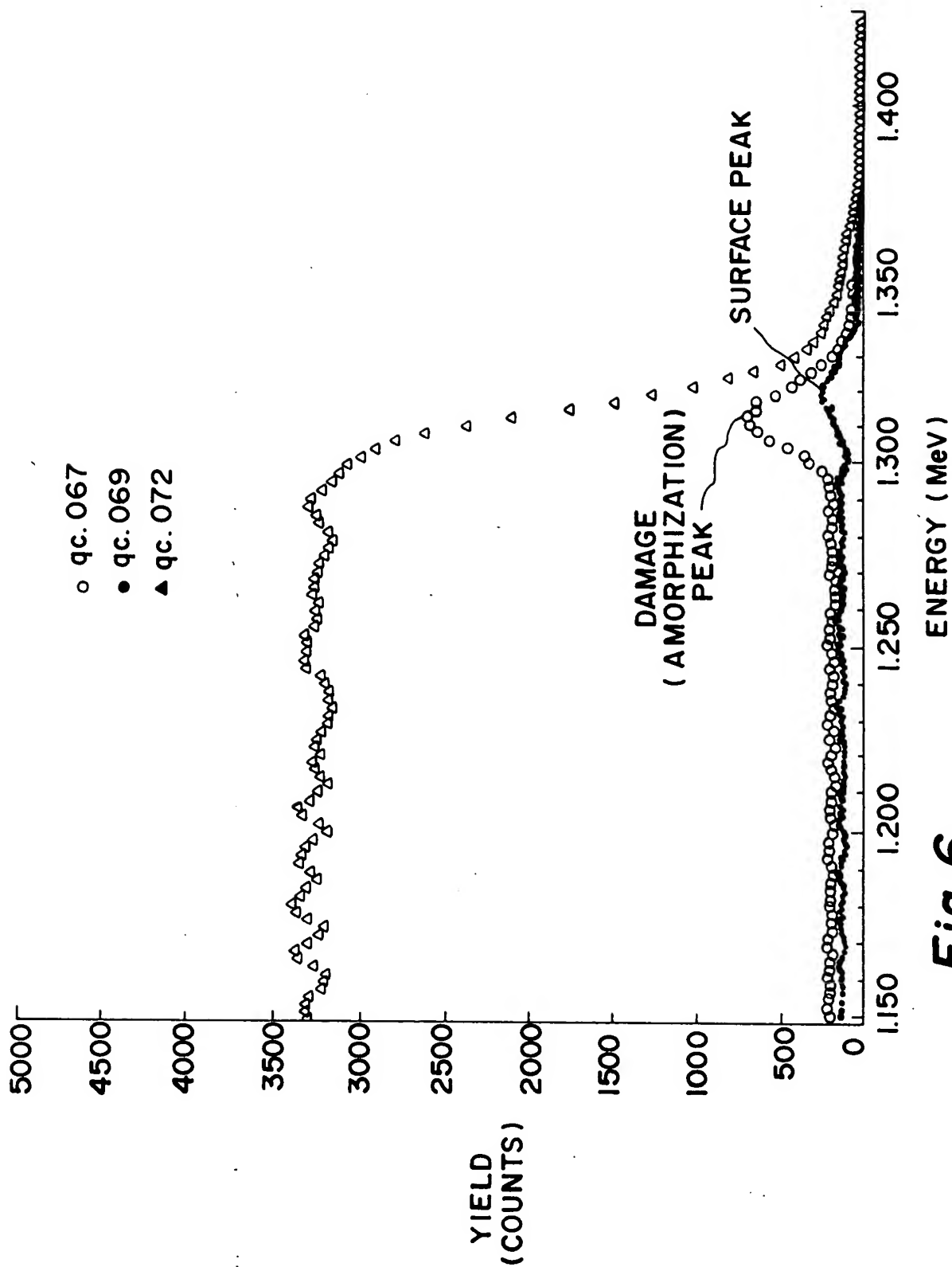


Fig. 6



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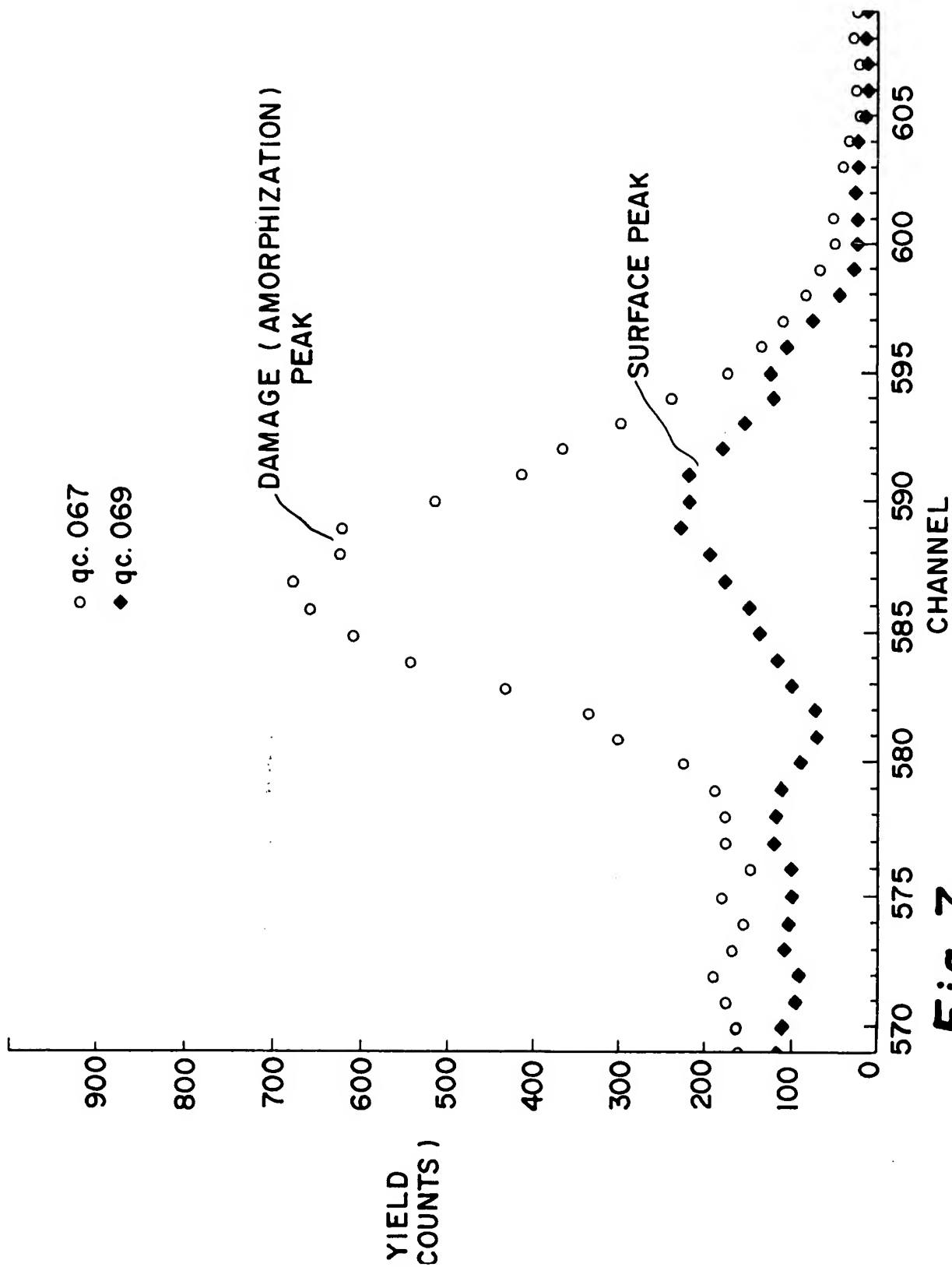


Fig. 7

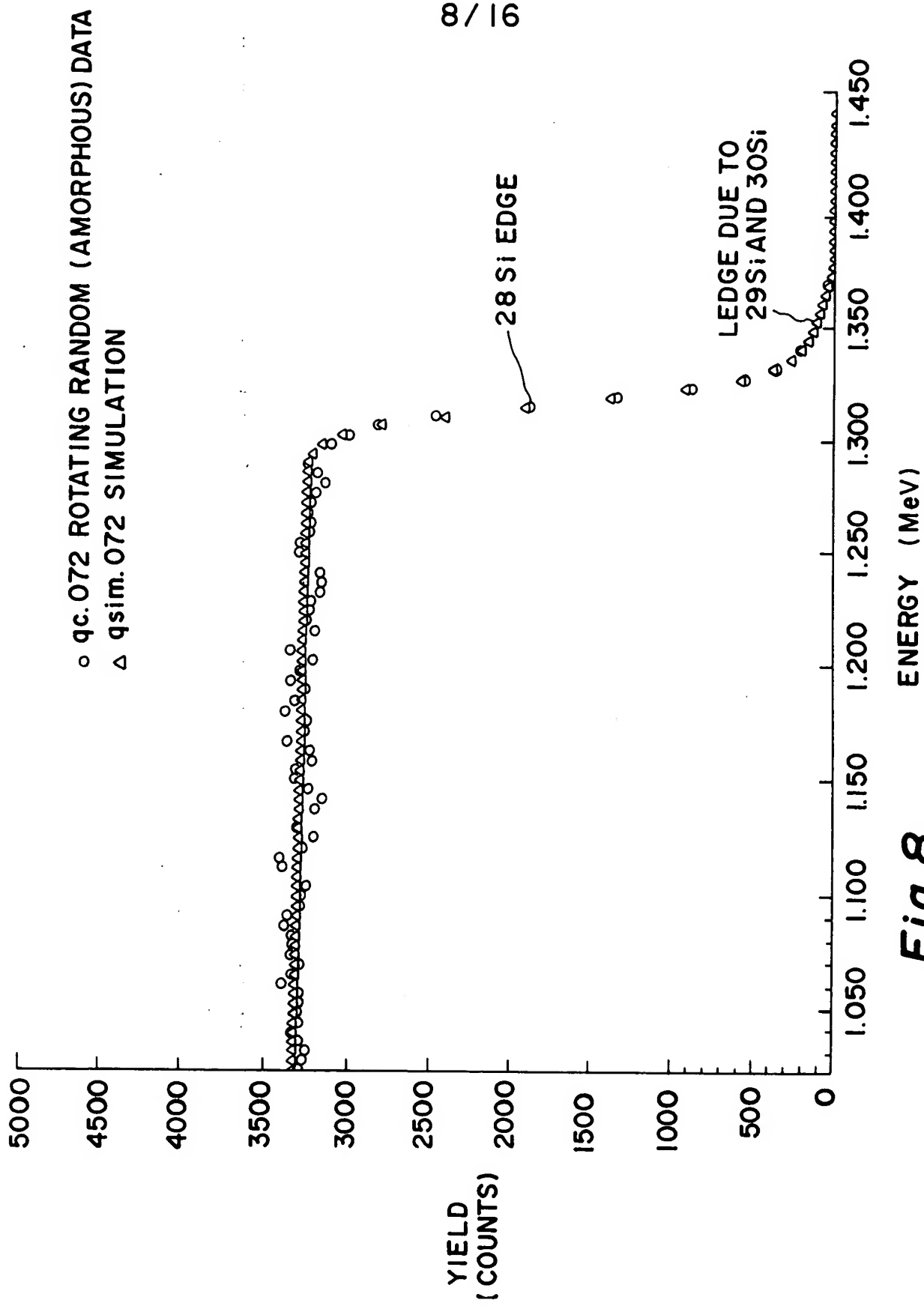


Fig. 8



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qpeak.067-STRIPPED PEAK DATA FROM Fig. 5 qc.
qsim.067-SIMULATION FOR 92 ANGSTROM
AMORPHOUS Si LAYER USING
PARAMETER DERIVED IN Fig.6

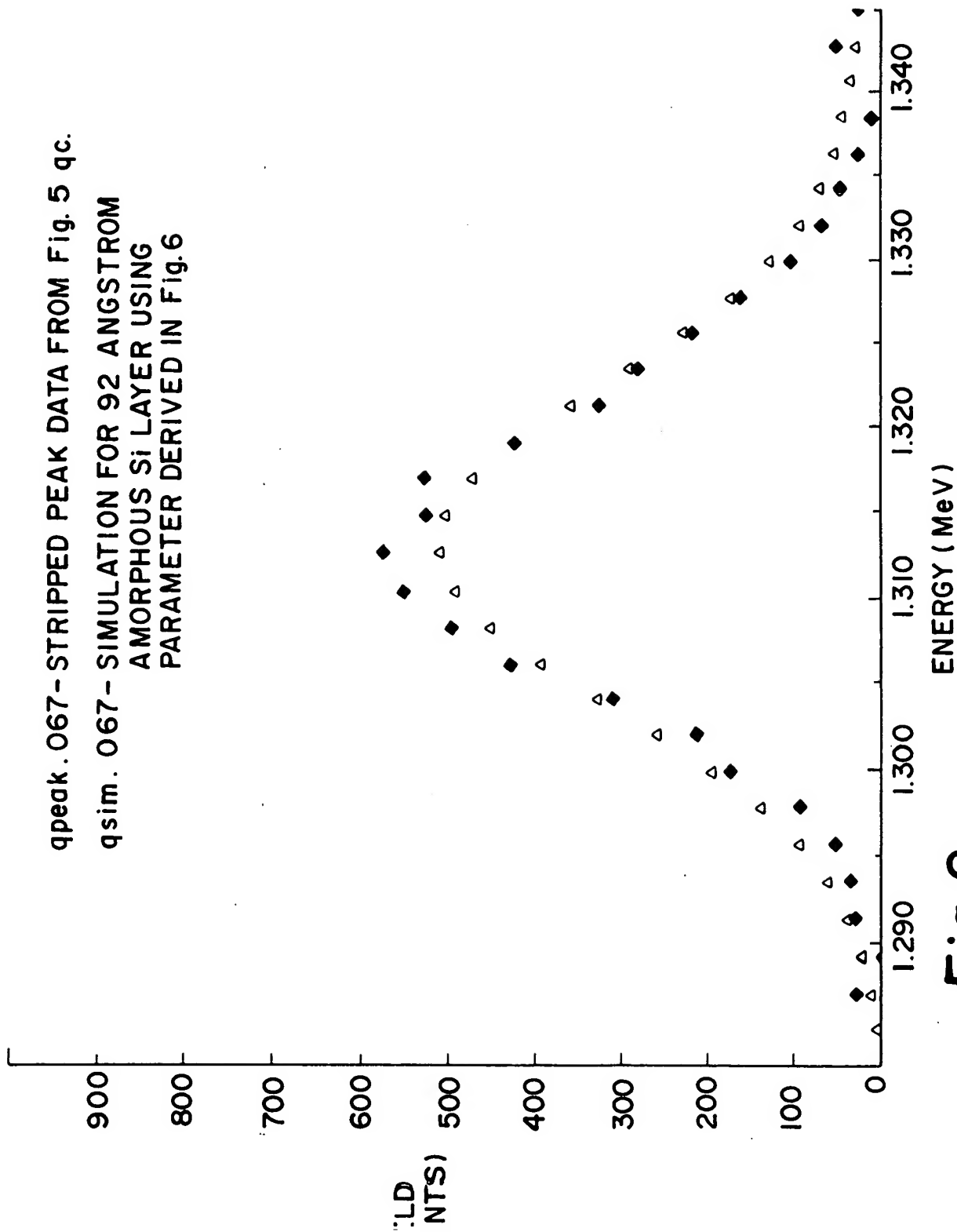


Fig.9

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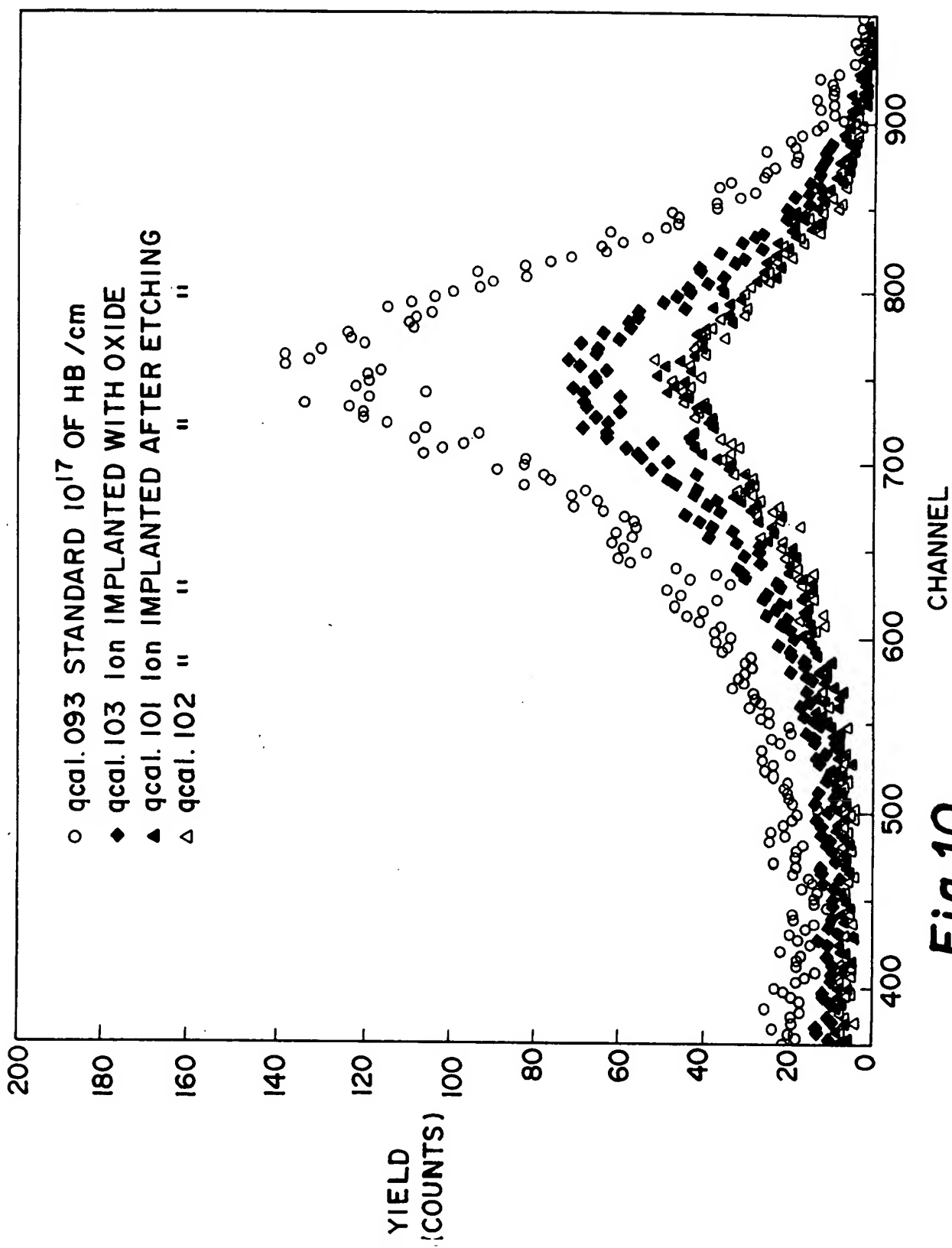


Fig.10



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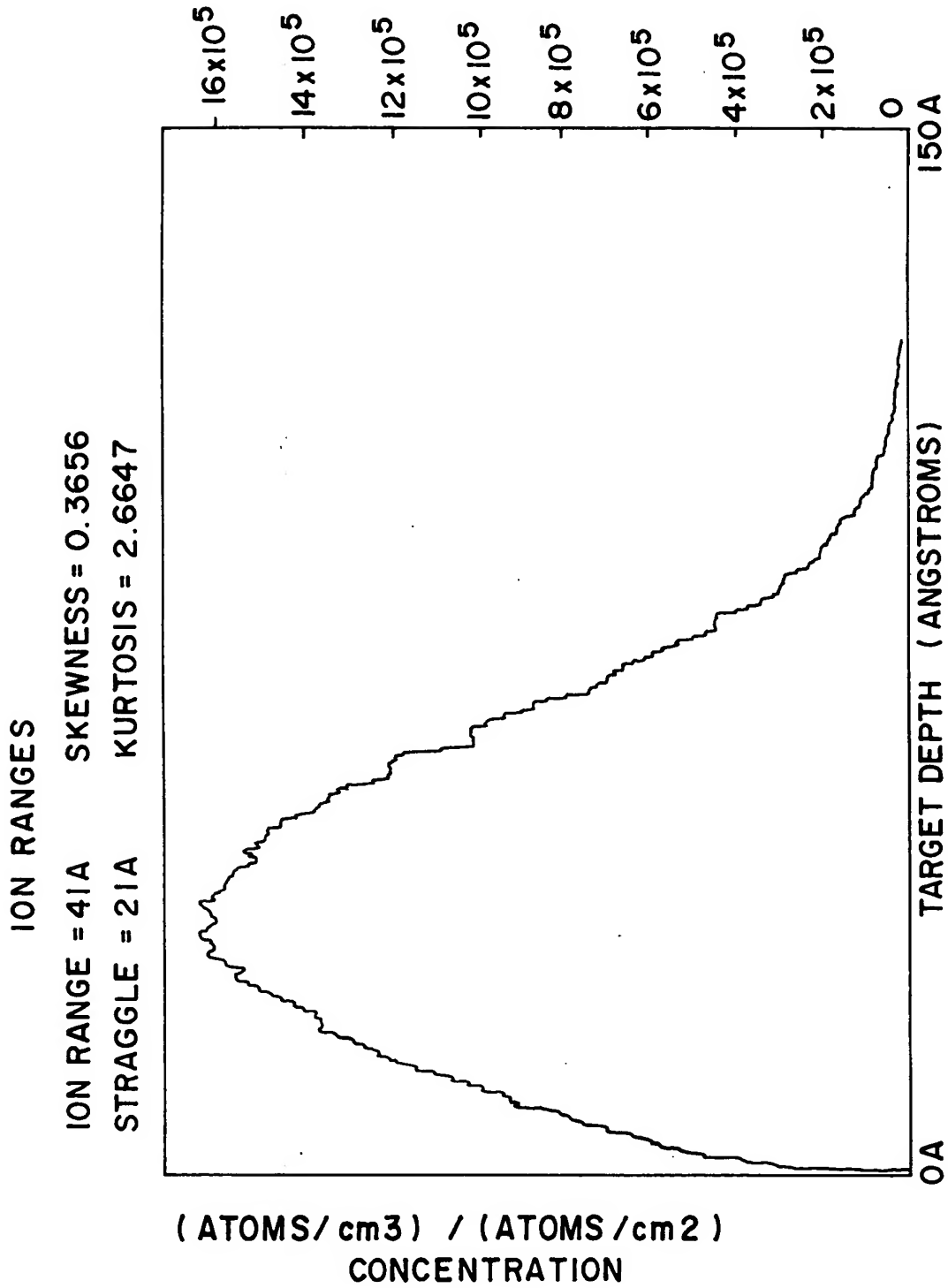
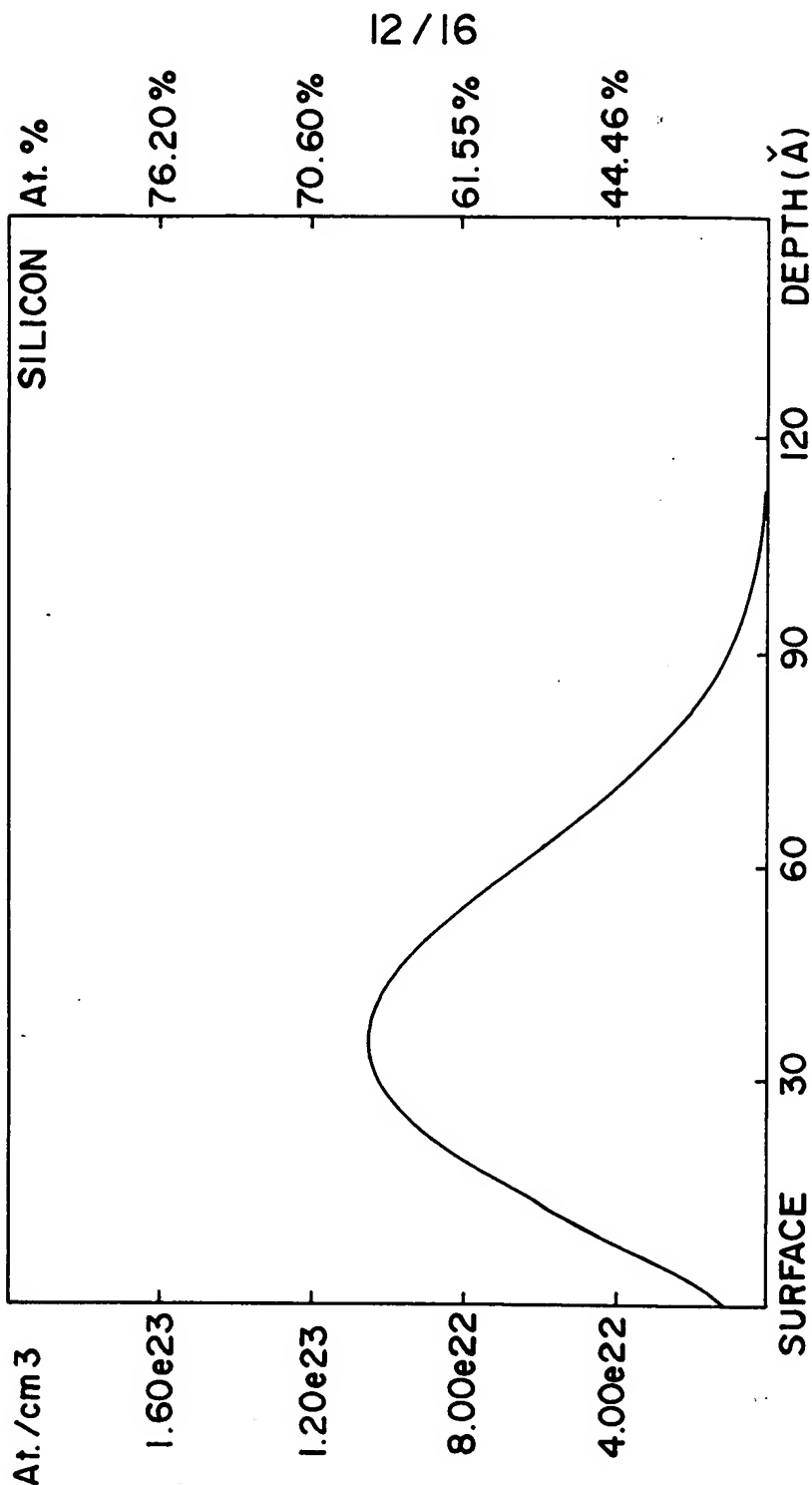


Fig. 11



TARGET= SILICON 2.33G 0° keV Ion Dose/cm2				
Calc.	Type	Planar, Pearson IV	1	6
Peak	Data	35Å 1.05e23 67.8%	2	7
Sput.	Loss	Coef= .000 Tot.= 0Å	3	8
Retn.	Doss	5.84e16/cm2 97.4%	4	9
			5	10



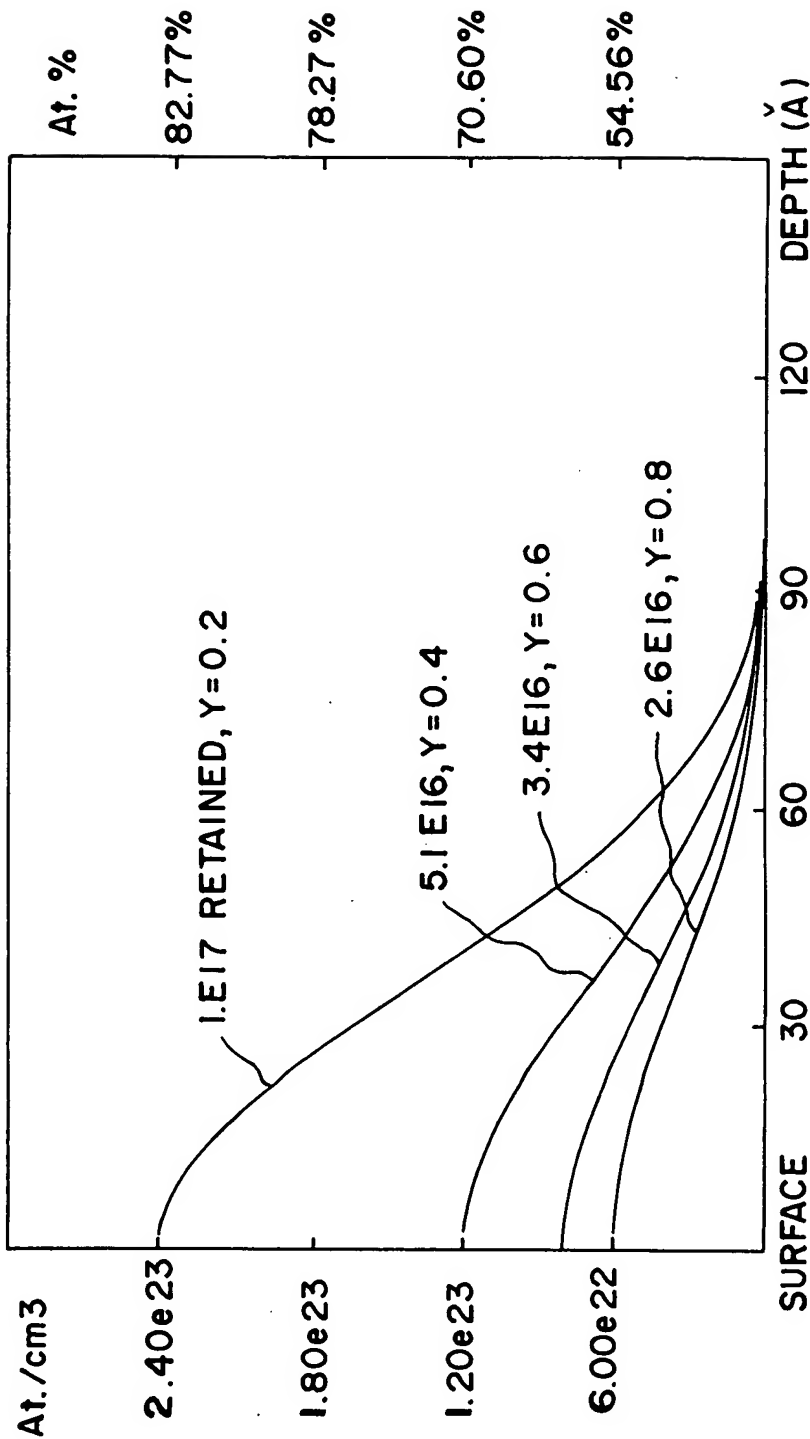
PROFILE
CODE

Fig.12



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TARGET=		SILICON	2.33G	0°	keV	Ion	Dose/cm2	keV	Ion	Dose/cm2
Calc.	Type	Planar, Pearson IV		1	2B	-11	4.00e17	6		
Peak	Data	0A 6.07e22 54.9%		2	2B	-11	4.00e17	7		
Sput.	Loss	Coef=.800 Tot.=641A		3	2B	-11	4.00e17	8		
Retn.	Doss	2.56e16/cm2 6.4%		4	2B	-11	4.00e17	9		
				5				10		



PROFILE
CODE

Fig.13

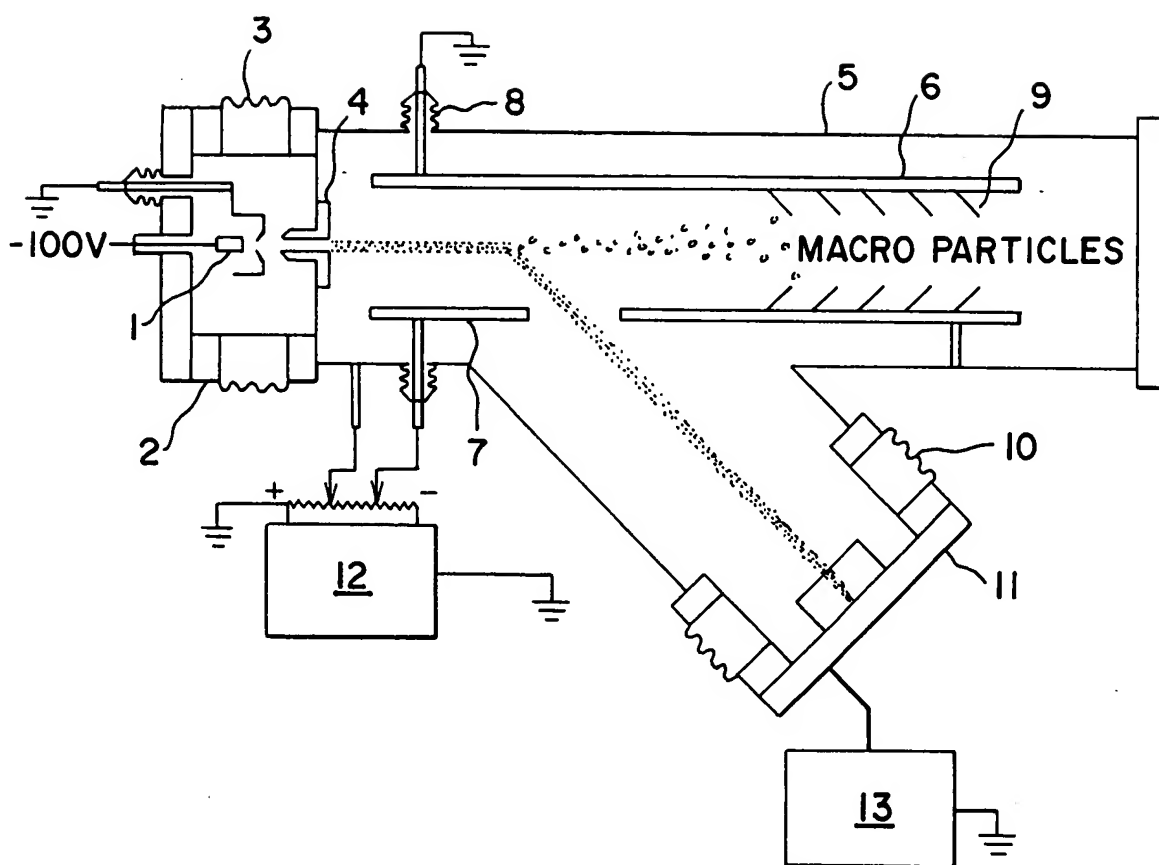


Fig. 14

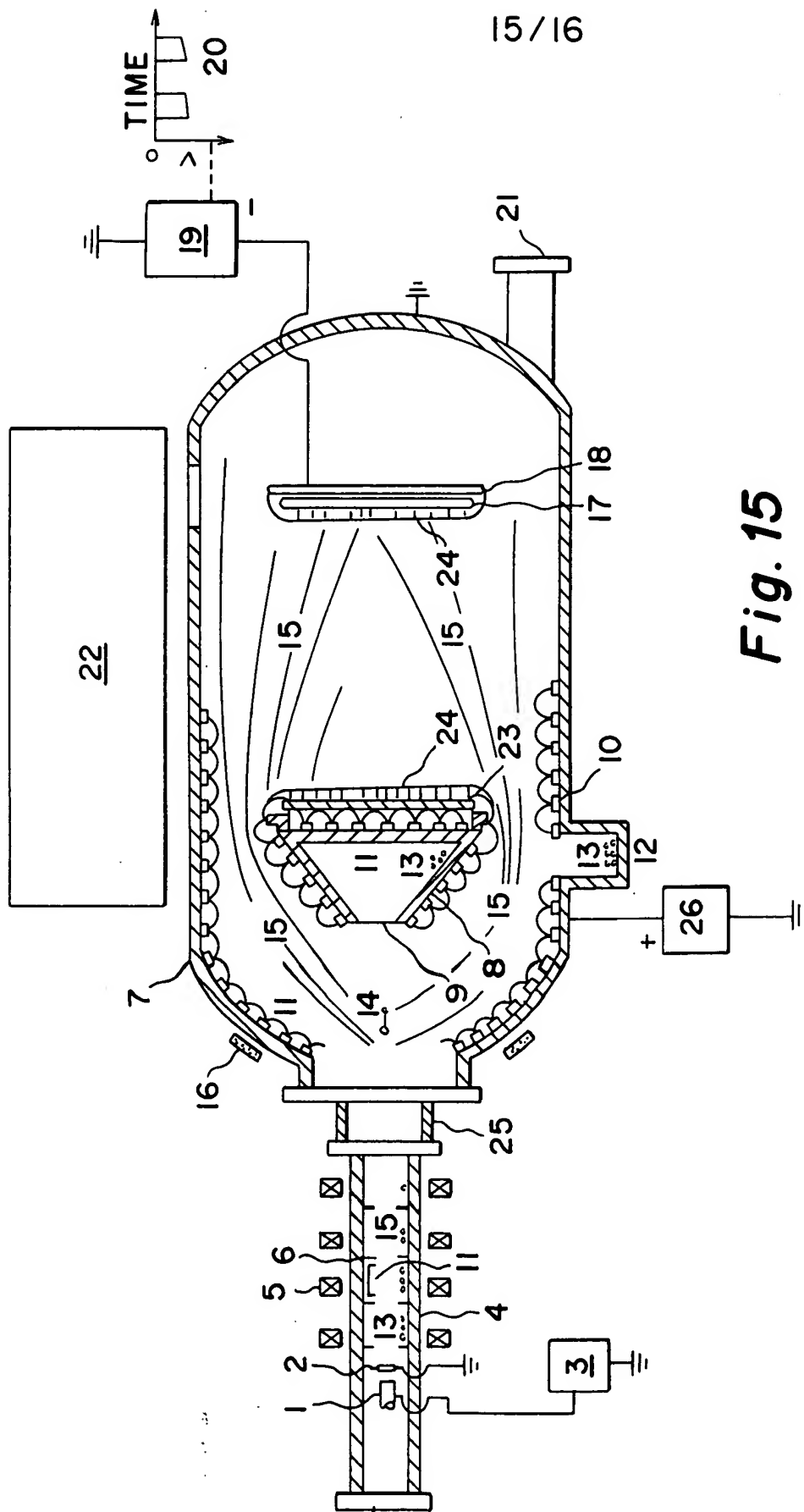


Fig. 15

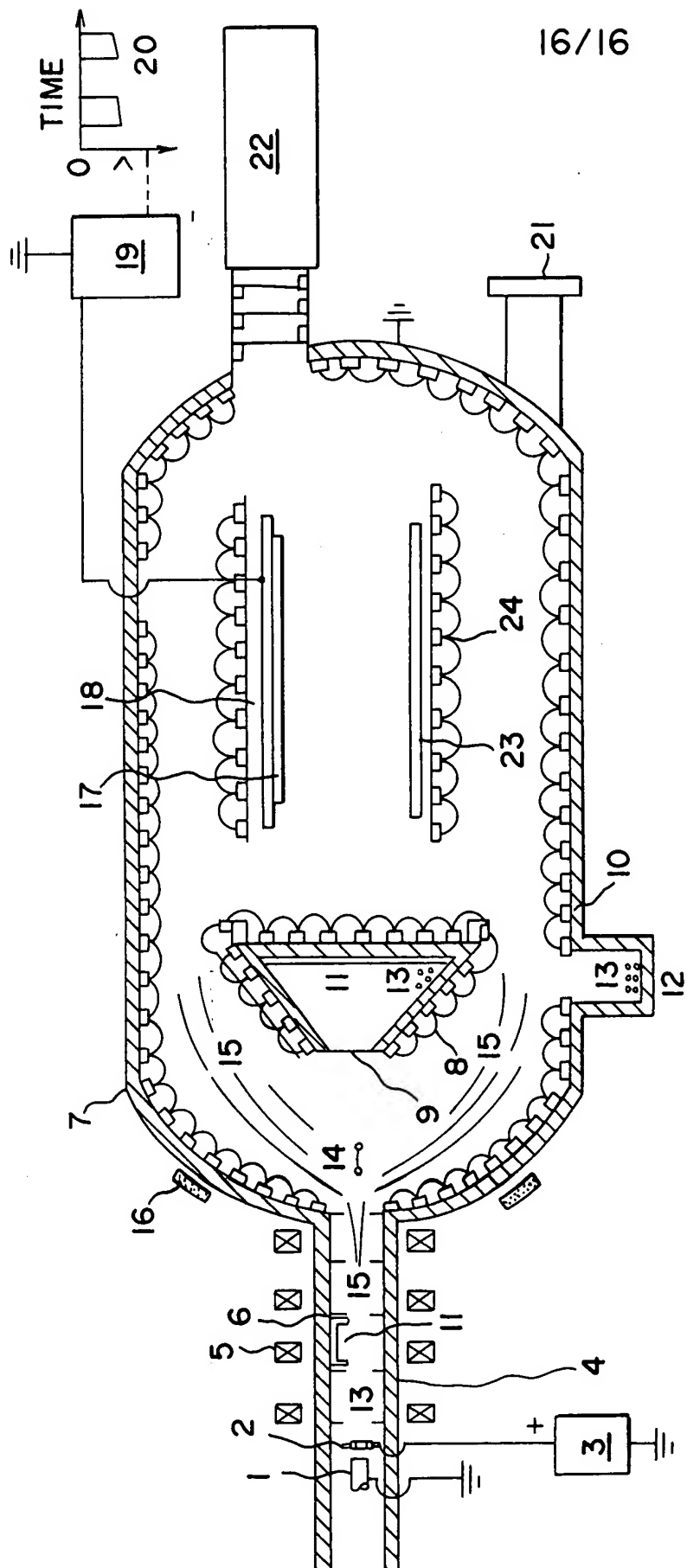


Fig. 16